OPB825, OPB825A

Obsolete (OPB825B, OPB825R)

Features:

- Non-contact switching
- Fast switching speed
- 0.160" (4.06 mm) wide slot
- 0.300" (7.62 mm) lead spacing





Description:

Each OPB825 and OPB825A have an infrared LED. All devices have a NPN silicon phototransistor mounted in a low-cost black plastic housing on opposite sides of a 0.160" (4.064 mm) wide slot.

OPB825 have no mounting tabs and is intended for direct insertion into PCBoards or dual-in-line sockets. OPB825A has one mounting tab on the phototransistor side.

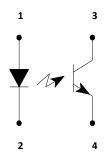
Phototransistor switching takes place whenever an opaque object passes through the slot.

Applications:

- Non-contact interruptive object sensing
- Assembly line automation
- Machine automation
- Equipment security
- Machine safety
- Ticket Sensing

Ordering Information					
Part Number	Description				
OPB825	Slotted Switch (no tabs) IR-LED				
OPB825A	Slotted Switch (one tab) IR-LED				
OPB825B Obsolete	Slotted Switch (two tabs) IR-LED				
OPB825R Obsolete	Slotted Switch (no tabs) Red-LED				

Pin #	Description	Pin #	Description
1	Anode	3	Collector
2	Cathode	4	Emitter





General Note

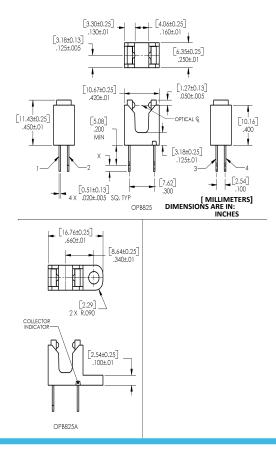
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Electrical Specifications

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Storage & Operating Temperature Range	-40° C to +85° C			
Lead Soldering Temperature [1/16 inch (1.6 mm) from the case for 5 sec. v	260° C			
Input Diode OPB8		25—A		
Forward DC Current 50 mA		A		
Peak Forward Current (1 μ s pulse width, 300 pps)	3 A	3 A		
Reverse DC Voltage	2 V	2 V		
Power Dissipation ⁽²⁾	100 m	100 mW		
Output Phototransistor	25—A			
Collector-Emitter Voltage	30 \	30 V		
Emitter-Collector Voltage	5 V	5 V		
Collector DC Current	30 m	30 mA		
Power Dissipation ⁽²⁾	100 m	100 mW		



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Electrical Specifications

OPB825, OPB825A

Electrical Characteristics (T_A = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	ТҮР	ΜΑΧ	UNITS	TEST CONDITIONS			
Input Diode	Input Diode (See OP240 for additional information)								
V _F	Forward Voltage	-	-	1.6	V	I _F = 20 mA			
I _R	Reverse Current		-	100	μΑ	V _R = 2 V			
Output Pho	Output Phototransistor (See OP550 for additional information)								
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	-	-	V	I _c = 1 mA			
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5	-	-	V	Ι _E = 100 μΑ			
I _{CEO}	Collector Dark Current	-	-	100	nA	$V_{CE} = 10 V, I_F = 0, E_E = 0$			
Combined									
V _{CE(SAT)}	Collector-Emitter Saturation	-	-	0.4	V	I _C = 250 μA, I _F = 20 mA			
I _{C(ON)}	On-State Collector Current	1.0	-	-	mA	I _F = 20 mA, V _{CE} = 10 V			

Notes:

(1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.

(2) Derate linearly 1.67 mW/°C above 25° C.

(3) All parameters tested using pulse techniques.

(4) Methanol or isopropanol are recommended as cleaning agents. Plastic housing is soluble in chlorinated hydrocarbons and ketones.

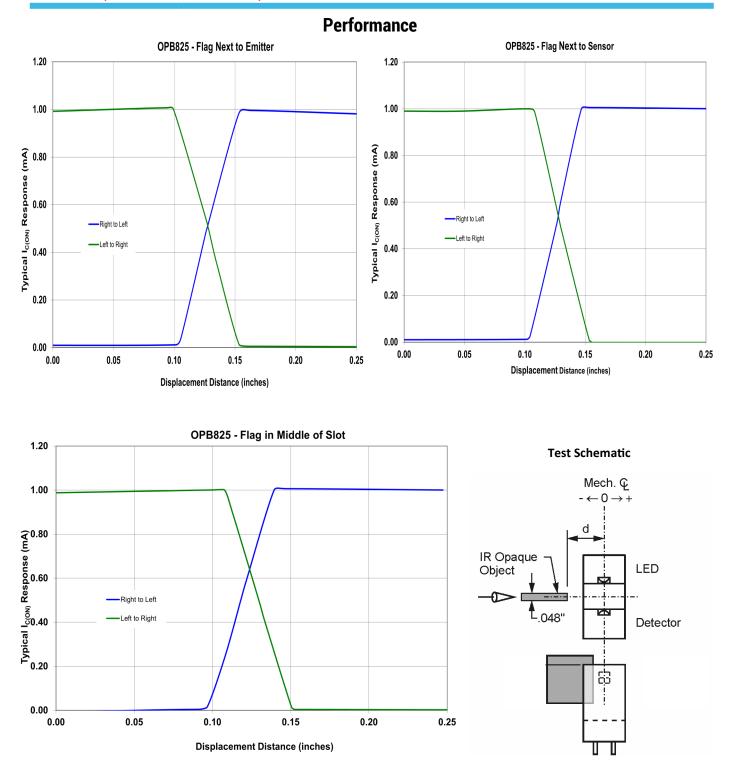
(5) Simulates optical path blocked with thick paper.

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OPB825, OPB825A Obsolete (OPB825B, OPB825R)





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